WHAT IS CLAIMED IS:

1. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming an insulating film spacer only on the sidewall of conductive layer patterns at a region where a contact plug will be formed and then forming an interlayer dielectric film on the entire surface.

2. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 1, wherein said conductive layer patterns are word lines or bit lines.

3. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming conductive layer patterns of a given pattern and an insulating film spacer on the sidewalls of said conductive layer patterns through a common process;

removing said insulating film spacer formed in a region other than a region where a contact plug will be formed; and

forming an interlayer dielectric film on the entire surface.

4. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 3, wherein said conductive layer patterns are word lines or bit lines.

5. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming conductive layer patterns of a given pattern through a common process;

forming an interlayer dielectric film on the entire surface; and

removing said interlayer dielectric film at a region where a contact plug will be formed and then forming an insulating film spacer on the sidewall of said conductive layer patterns.

6. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 5, wherein said conductive layer patterns are word lines or bit line.

7. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming conductive layer patterns of a given pattern and an insulating film spacer on the sidewall of said conductive layer patterns through a common process;

burying a conductive material between said conductive layer patterns;

removing said conductive material only at a given region and remaining said conductive material at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer

patterns at a region from which said conductive material is removed.

8. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 7, wherein said conductive layer patterns are word lines or bit lines.